

Darlington Power Transistor



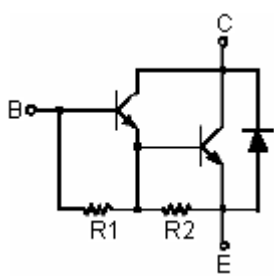
Features:

- Silicon PNP
- Darlington
- High DC current gain

Application:

For use as output devices in complementary general - purpose amplifier applications

Fig. 1 Simplified Outline (TO-126) and Symbol



Pinning

Pin	Description
1	Emitter
2	Collector; connected to mounting base
3	Base

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Symbol	Parameter	Conditions	Value	Unit
V_{CBO}	Collector - base voltage	Open emitter	-80	V
V_{CEO}	Collector - emitter voltage	Open base	-80	V
V_{EBO}	Emitter - base voltage	Open collector	-5	V
I_C	Collector current	-	-4	A
I_B	Base current	-	-0.1	A
P_C	Collector power dissipation	$T_C = 25^\circ\text{C}$	40	W
T_j	Junction temperature	-	150	$^\circ\text{C}$
T_{stg}	Storage temperature	-	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Maximum	Unit
$R_{th\ j-c}$	Thermal resistance junction to case	3.13	$^\circ\text{C/W}$

Characteristics ($T_j = 25^\circ\text{C}$ Unless Otherwise Specified)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
$V_{(BR)\ CEO}$	Collector - emitter breakdown voltage	$I_C = -50\text{ mA}; I_B = 0$	-80	-	-	V
$V_{(BR)\ CBO}$	Collector - base breakdown voltage	$I_C = -1\text{ mA}; I_E = 0$	-80	-	-	V
$V_{(BR)\ EBO}$	Emitter - base breakdown voltage	$I_E = -5\text{ mA}; I_C = 0$	-5	-	-	V

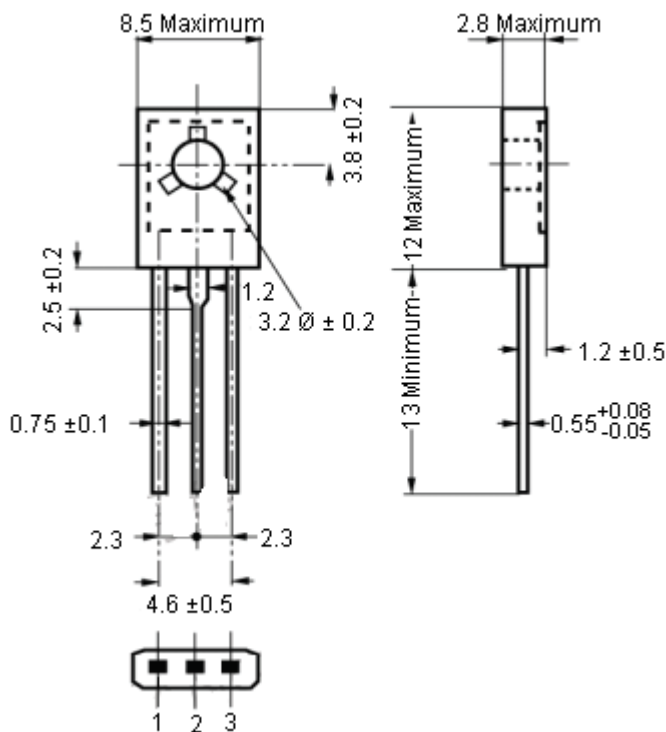
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Characteristics ($T_j = 25^\circ\text{C}$ Unless Otherwise Specified)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
V_{CEsat}	Collector - emitter saturation voltage	$I_C = -1.5\text{ A}$; $I_B = 30\text{ mA}$	-	-	-2.5	V
$V_{BE(on)}$	Base - emitter on voltage	$I_C = -1.5\text{ A}$; $V_{CE} = -3\text{ V}$	-	-	-2.5	V
I_{CBO}	Collector cut-off current	$V_{CB} = \text{Rated } BV_{CEO}$; $I_E = 0$ $T_a = 100^\circ\text{C}$	-	-	-0.2 -2	mA
I_{CEO}	Collector cut-off current	$V_{CE} = 1/2 \text{ rated } BV_{CEO}$; $I_B = 0$	-	-	-0.5	mA
I_{EBO}	Emitter cut-off current	$V_{EB} = 5\text{ V}$; $I_C = 0$	-	-	-2	mA
h_{FE}	DC current gain	$I_C = -1.5\text{ A}$; $V_{CE} = -3\text{ V}$	750	-	-	-

Package Outline



Dimensions : Millimetres

Fig. 2 Outline Dimensions

Part Number Table

Description	Part Number
Silicon PNP Darlington Power Transistor	BD680

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